

High-Speed Dual Pin Electronic

AD53522

FEATURES

1000 MHz Toggle Rate
Driver/Comparator/Active Load and Dynamic Clamp
Included

Inhibit Mode Function 100-Lead LQFP Package with Built-In Heat Sink Driver

48 Ω Output Resistance 800 ps Tr/Tf for a 3 V Step

Comparator

1.1 ns Propagation Delay at 3 V

Load

±40 mA Voltage Programmable Current Range 50 ns Settling Time to 15 mV

APPLICATIONS

Automatic Test Equipment Semiconductor Test Systems Board Test Systems Instrumentation and Characterization Equipment

PRODUCT DESCRIPTION

The AD53522 is a complete, high-speed, single-chip solution that performs the pin electronics functions of driver, comparator, and active load (DCL) for ATE applications. In addition, the driver contains a dynamic clamp function and the active load contains an integrated Schottky diode bridge.

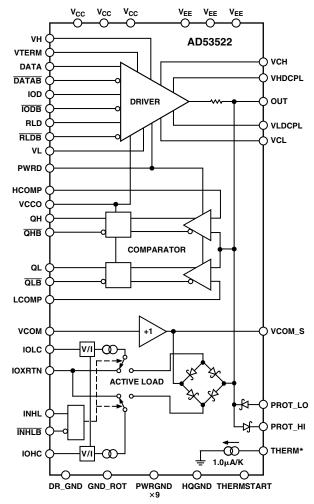
The driver is a proprietary design that features three active states: Data High Mode, Data Low Mode, and Term Mode, as well as an Inhibit State. In conjunction with the integrated dynamic clamp this facilitates the implementation of a high-speed active termination. The output voltage range is -0.5 V to +6.5 V to accommodate a wide variety of test devices.

The dual comparator, with an input range equal to the driver output range, features PECL compatible outputs. Signal tracking capability is in the range of 3 V/ns.

The active load can be set for up to 40 mA load current. I_{OH} , I_{OL} , and the buffered VCOM are independently adjustable. On-board Schottky diodes provide high-speed switching and low capacitance.

Also included on the chip is an on-board temperature sensor that gives an indication of the silicon surface temperature of the DCL. This information can be used to measure θ_{JC} and θ_{JA}

FUNCTIONAL BLOCK DIAGRAM



*ONLY 1 (ONE) THERM PER DEVICE

or flag an alarm if proper cooling is lost. Output from the sensor is a current sink that is proportional to absolute temperature. The gain is trimmed to a nominal value of 1.0 μ A/k Ω . As an example, the output current can be sensed by using a 10 k Ω resistor connected from 10 V to the THERM (I_{OUT}) pin. A voltage drop across the resistor will be developed that equals: 10 k Ω × 1 μ A/k Ω = 10 μ V/k Ω = 2.98 V at room temperature.

AD53522—SPECIFICATIONS

Spec No.	Parameter	Conditions	Min	Typ ²	Max	Unit	Spec ³ Perf
	DIFFERENTIAL INPUT CHARAGE (DATA to DATAb, IOD to IODb, RLD to RLDb)	CTERISTICS					
1	Voltage Range	Note: Inputs are from Same Logic Type Family	0		+3.3	V	N
2	Differential Voltage with LVPECL levels	Differential Voltage with Note: AC Tests Performed $\pm 400 \pm 600 \pm$		±1000	mV	P	
3	Bias Current	$V_{IN} = 1.5 \text{ V}, 2.5 \text{ V}$	-250		+250	μΑ	P
4	REFERENCE INPUTS Bias Currents	Max Value Measured During Linearity Tests	-50		+50	μΑ	P
10	OUTPUT CHARACTERISTICS Logic High Range	Data = H, VH = -0.4 V to $+6.5$ V, VI = -0.5 V (VT = 0 V, VH meets test 20, 21, and 22 specs)	-0.4		+6.5	V	P
11	Logic Low Range	Data = L, $VL = -0.5 V$ to +6.4 V, VH = 6.5 V ($VT = 0 V$, VL meets	-0.5		+6.4	V	P
12	Amplitude [VH–VL]	test 30, 31, and 32 specs) VL = -0.05 V, VH = +0.05 V, VT = 0 V and VL = -0.5 V, VH = +6.5 V, VT = 0 V	+0.1		+7.0	V	P
	ABSOLUTE ACCURACY						
20	VH Offset	Data = H, VH = 0 V, VL = -0.5 V, VT = $+3$ V	-50		+50	mV	P
21	VH Gain Error	Data = H, VH = -0.4 V to $+6.5$ V, VL = -0.5 V, VT = $+3$ V	-0.3		+0.3	% of VH	P
22	Linearity Error	Data = H, VH = -0.4 V to $+6.5$ V, VL = -0.5 V, VT = $+3$ V	-5		+5	mV	P
30	VL Offset	Data = L, VL = 0 V, VH = 6.5 V, VT = 3 V	-50		+50	mV	P
31	VL Gain Error	Data = L, $VL = -0.5 V$ to +6.4 V, VH = +6.5 V, $VT = +3 V$	-0.3		+0.3	% of VL	P
32	Linearity Error	Data = L, VL = -0.5 V to +6.4 V, VH = +6.5 V, VT = +3 V	- 5		+5	mV	P
33	Offset Temperature Coefficient	VL = 0 V, VH = 5 V, VT = 0 V		0.5		mV/°C	N
40	OUTPUT RESISTANCE VH = -0.3 V	$VL = -0.5 \text{ V}, VT = 0 \text{ V}, I_{OUT} = +1,$ +30 mA	+46		+50	Ω	N
41	VH = +6.5 V	$VL = -0.5 \text{ V}, VT = 0 \text{ V}, I_{OUT} = -1,$ -30 mA	+46		+50	Ω	P
42	VL = -0.5 V	$VH = +6.5 \text{ V}, VT = 0 \text{ V}, I_{OUT} = +1,$ +30 mA	+46		+50	Ω	P
43	VL = +6.4 V	$VH = +6.5 \text{ V}, VT = 0 \text{ V}, I_{OUT} = -1,$ -30 mA	+46		+50	Ω	N
44	VH = +2.5 V	$VL = 0 \text{ V}, VT = 0 \text{ V}, I_{OUT} = -30 \text{ mA}$ (Trim Point)		+47.5		Ω	P
50	Dynamic Current Limit	Cbyp = 39 nF, VH = +6.5 V, VL = -0.5 V, VT = 0 V	+100			mA	N
51	Static Current Limit	Output to -0.5 V, VT = 0 V, VL = -0.5 V, VT = 0 V, DATA = H	-120		-60	mA	P
52	Static Current Limit	Output to +6.5 V, VH = +6.5 V, VL = -0.5 V, VT = 0 V, DATA = L	+60		+120	mA	P

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Spec No.	Parameter	Conditions	Min	Typ ²	Max	Unit	Spec ³ Perf
	VTERM						
60	Voltage Range	TERM MODE, VTERM = -0.3 V	-0.3		+6.3	V	P
		to $+6.3 \text{ V}$, $\text{VL} = 0 \text{ V}$, $\text{VH} = +3 \text{ V}$					
		(VTERM meets test 61, 62,					
		and 63 specs)					_
61	VTERM Offset	TERM MODE, VTERM = 0 V,	-50		+50	mV	P
60	WEEDIN Coin France	VL = 0 V, VH = 3 V	0.2		10.2	0/ - 637	D.
62	VTERM Gain Error	TERM MODE, VTERM = -0.3 V to +6.3 V, VL = 0 V, VH = +3 V	-0.3		+0.3	% of V _{SET}	P
63	VTERM Linearity Error	TERM MODE, VTERM = -0.3 V	-5		+5	mV	P
03	VIEWVIEMCATRY ETFOR	to +6.3 V, VL = 0 V, VH = +3 V	_5		13	111 4	*
64	Offset Temperature Coefficient	VTERM = 0 V, VL = 0 V, VH = 3 V		+0.5		mV/°C	N
70	Output Resistance DC	I_{OUT} = +30 mA, -1 mA, VTERM =	+46		+50	Ω	
		-0.3 V, VH = 3 V, VL = 0 V					N
		$I_{OUT} = -30 \text{ mA}$, +1 mA, VTERM =					
		+6.3 V, VH = 3 V, VL = 0 V					N
		$I_{OUT} = \pm 30 \text{ mA}, \pm 1 \text{ mA}, \text{VTERM} =$					
		+2.5 V, VH = 3 V, VL = 0 V					P
72	PSRR, Drive, or TERM Mode	$+V_S$, $-V_S \pm 1\%$		17.8		mV/V	N
73	Static Current Limit	Output to -0.3 V, VTERM = +6.3 V			-60	mA	P
74	Static Current Limit	Output to $+6.3 \text{ V}$, VTERM = -0.3 V	+60		+120	mA	P
	DYNAMIC PERFORMANCE, DR	IVE					
	(VH and VL)						
80	Propagation Delay Time	Measured at 50% , VL = 0 V,	1.25	1.4	1.55	ns	P
		VH = 3 V, into 500 Ω		_		, a	
81	Propagation Delay T.C.	Measured at 50% , VL = 0 V,		2		ps/°C	N
82	Delay Matching, Edge-to-Edge	VH = 3 V, into 500 Ω			200		P
02	Delay Matching, Edge-to-Edge	Measured at 50%, VL = 0 V, VH = 3 V, into 500 Ω			200	ps	r
		V11 = 3 V, Into 300 22					
	RISE AND FALL TIMES						
90	200 mV Swing	Measured 20%–80%, VL = -0.1 V ,		0.25		ns	N
0.1	1 V Coming	VH = +0.1 V, into 50 Ω		0.2			NT.
91	1 V Swing	Measured 20%–80%, VL = 0 V, VH = 1 V, into 50 Ω		0.3		ns	N
92	3 V Swing	Measured $10\%-90\%$, VL = 0 V,		0.8		ns	N
92	J V Swing	VH = 3 V, into 50 Ω		0.0		113	1
93	3 V Swing	Measured $10\%-90\%$, VL = 0 V,		0.8		ns	N
, ,	J V U Mag	VH = 3 V, into 500 Ω		0.0		110	- '
93A	3 V Swing	Measured $20\%-80\%$, VL = 0 V,	0.450	0.560	0.670	ns	P
		VH = 3 V, into 500 Ω					
94	5 V Swing	Measured $10\%-90\%$, VL = 0 V,		1.2	1.5	ns	N
		VH = 5 V, into 500 Ω					
	RISE AND FALL TIME TEMPER	ATURE COEFFICIENT					
100	1 V Swing	(per test 91)		±2		ps/°C	N
101	3 V Swing	(per test 92)		±2		ps/°C	N
102	5 V Swing	(per test 94)		± 4		ps/°C	N
110	Overshoot and Preshoot	VL, $VH = -0.1 V$, $+0.1 V$,	0 – 50		0 + 50	% of Step	N
		Driver Terminated into 50 Ω				+ mV	
		VL, VH = 0.0 V, 3 V,	-6.0 - 50)	+6.0 + 50	% of Step	N
		Driver Terminated into 50 Ω				+ mV	
-	SETTING TIME						
120	to 15 mV	VL = 0 V, $VH = 0.5 V$, Driver		50		ns	N
-		Terminated into 50 Ω					

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SPECIFICATIONS (continued)

$DRIVER^1 \ \ ({\tt continued})$

Spec No.	Parameter	Conditions	Min Typ ²	Max	Unit	Spec ³ Perf
130	Delay Change vs. Pulsewidth 30 ns/90 ns, DC = 25%	VL/VH = 0/3, $PW = 2.5 ns/7.5 ns$,	25	75	ps	N
131	Delay Change vs. Duty Cycle	VL = 0 V, VH = 3 V, Duty Cycle (DC) 5 to 95%, T = 40 ns	25		ps	N
140	MINIMUM WIDTH PULSE 1 V Swing	Meas 50% point width V_{OUT} AC Swing = 0.9 × V_{OUT} DC	0.6	0.6		N
141	3 V Swing	Swing Terminated, 50 Ω Load on Transmission Line	1.5		ns	N
142	Toggle Rate	VH = 1 V, VL = 0 V, Terminated to 50 Ω , V _{OUT} > 300 mV p-p	1000		MHz	N
	DYNAMIC PERFORMANCE, IN					
150	Delay Time, Active to Inhibit	Measured at 50%, VH = 4 V, VL = 0 V, VTT = 2	1.7	2.0	ns	P
151	Delay Time, Inhibit to Active	Measured at 50%, VH = 4 V, VL = 0 V, VTT = 2	1.7	2.2	ns	P
152	Delay Time Matching, Inhibit to Active	Measured at 50%, VH = 4 V, VL = 0 V, VTT = 2	150	250	ps	P
153	Delay Time Matching, Active to Inhibit	Measured at 50%, $VH = 4 V$,	150	250	ps	P
160	I/O Spike	VL = 0 V, VTT = 2 VH = 0 V, VL = 0 V		200	mV p-p	N
170	Rise, Fall Time, Active to Inhibit	VL = 0 V, VTT = 2 (20%/80%		1.2	ns	N
171	Rise, Fall Time, Inhibit to Active	of 1 V Output) VH = 4 V, VL = 0 V, VTT = 2 (20%/80% of 1 V Output)		0.6	ns	N
	DVNIAMIC DEDECTMANICE VI	+				
180	DYNAMIC PERFORMANCE, VI Delay Time, VH to VTERM	Measured at 50%, VL = VH = 2 V, VTERM = 0 V, VTT = 0 V	1.5	1.9	ns	P
181	Delay Time, VL to VTERM	Measured at 50%, VL = VH = 0 V, VTERM = 2 V, VTT = 0 V	1.6	1.9	ns	P
182	Delay Time, VTERM to VH	Measured at 50%, VL = VH = 2 V, VTERM = 0 V, VTT = 0 V	1.6	2.0	ns	P
183	Delay Time, VTERM to VL	Measured at 50%, VL = VH = 0 V, VTERM = 2 V, VTT = 0 V	1.6	2.0	ns	P
190	Overshoot and Preshoot	VH/VL, VTERM = (0 V, 2 V), (0 V, 6 V)	-6.0 + 50	+6.0 + 50	% of Step + mV	N
191A	VTERM Rise Time, VL to VT, Normal Mode	VL, VH = 0 V, VTERM = 2 V, 20%-80%		1.0	ns	N
191B	VTERM Rise Time, VT to VH, Normal Mode	VL, VH = 2 V, VTERM = 0 V, 20%-80%		0.6	ns	N
192A	VTERM Fall Time, VT to VL, Normal Mode	VL, VH = 0 V, VTERM = 2 V, 20%-80%		0.6	ns	N
192B	VTERM Fall Time, VH to VT, Normal Mode	VL, VH = 2V, VTERM = 0 V, 20%–80%		1.0	ns	N

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COMPARATOR¹

Spec No.	Parameter	Conditions	Min	Typ ²	Max	Unit	Spec ³ Perf
	DC INPUT CHARACTERISTICS						
200	VCCO Range		2.0		4.5		N
201	Offset Voltage (Vos)	Common-Mode Voltage = 0 V	-25		+25	mV	P
202	Offset Voltage Drift	Common-Mode Voltage = 0 V		50		μV/°C	N
203	HCOMP, LCOMP	Over Linearity Range	-50		+50	μA	P
	BIAS CURRENTS						
206	Voltage Range (V _{CM})		-0.5		+6.5	V	P
207	Differential Voltage (V _{DIFF})				+7	V	P
208	Gain Error	$V_{IN} = -0.5 \text{ V to } +6.5 \text{ V}$	-0.25		0.0	%FSR	N
209	Linearity Error	$V_{IN} = -0.5 \text{ V to } +6.5 \text{ V}$	-2		+2	mV	N
210	Extended Range Operation	HCOMP, LCOMP = -1, output	-1.0			V	P
	DIOMETE OF MEDITIES	toggle V _{OUT} from -0.9 V to -1.1 V					
220	DIGITAL OUTPUTS Logic "1" Voltage QX	Q or Qb, 150 Ω to GND,	VCCO	1.05	VCCO - 0.85	$ _{\mathbf{V}}$	P
220	Logic 1 Voltage QA	Ω or Q0, 150 Ω to Qb	VCCO.	-1.05	VCCO - 0.83	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	F
221	Logic "0" Voltage QXb	Q or Qb, 150 Ω to GND,	VCCO	2.2	VCCO - 1.5	$ _{V}$	P
221	Logic 0 Voltage QAb	150Ω from Q to Qb	VCCO	-2.2	VCCO - 1.5	\ \ \	1
222	Logic Differential, QX-QXb	Q or Qb, 150 Ω to GND,	0.65	0.9	1.15	V	P
	Logic Differential, QII QIIO	150Ω from Q to Qb	0.03	0.7	1.13	*	1
225	Slew Rate	Q or Qb (20 – 80% of output,		380		ps	N
		150 Ω from Q to Qb)					
	CHANNEL COMPARATOR SWIT	CCHING PERFORMANCE					
	PROPAGATION DELAY						
240	Input to Output	$V_{IN} = 3 \text{ V p-p, } 2 \text{ V/ns}$	0.7		1.1	ns	P
241	Propagation Delay Temp. Co.	$V_{IN} = 3 \text{ V p-p, } 2 \text{ V/ns}$		1.0		ps/°C	N
	Prop Delay Change with						
250	respect to:	V = 0 V = 2 V		100			\
250 260	Slew Rate: 1, 2, 3 V/ns Amplitude: 500 mV,	$V_{IN} = 0 V \text{ to } 3 V$		120		ps	N
200	1.0 V, 3.0 V	$V_{IN} = 1.0 \text{ V/ns}$		100		ps	N
270	Equivalent Input Rise Time	$V_{IN} = 1.0 \text{ V/Hs}$ $V_{IN} = 0 \text{ V to 2 V}, < 80 \text{ ps},$		275		ps ps	N
210	Equivalent input Rise Time	20%-80% Rise Time		213		Ps	1
		Driver in VTERM = 0 V					
280	Pulsewidth Linearity	$V_{IN} = 0 \text{ V to } 3 \text{ V}, 2 \text{ V/ns}, PW =$			50	ps	N
	1 also with Emourity	3, 4, 5, 10 ns, Driver Hi-Z mode			30		1
281	Settling Time	Settling to $\pm 8 \text{ mV}$, $V_{IN} = 0 \text{ V}$ to		25		ns	N
	S	3 V, Driver Hi-Z mode					
282	Hysteresis	-		6		mV	N
290	Comparator Propagation	$V_{IN} = 0 \text{ V to } 3 \text{ V}, 2 \text{ V/ns}$			125	ps	P
	Delay Matching, HCOMP						
	to LCOMP						
_	INPUT CHARACTERISTICS						
	INHL, INHLb	See Driver Spec No. 1					
300	Input Voltage	VIOH = 1 V, VIOL = 1 V,	0		3.3	V	P
201	DHH DHHI B' C	VCOM = 2 V, VDUT = 0 V	250		. 250		D
301	INHL, INHLb Bias Current	INHL, INHLb = 0 V, 3.3 V, AC Tests 0.2 V and 0.8 V	-250		+250	μΑ	P
302	VIOH Current Program Range,	VDUT = 0.8 V, 6.5 V	0		4.0	v	$ _{\mathbf{P}}$
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SPECIFICATIONS (continued)

ACTIVE LOAD¹

Spec No.	Parameter	Conditions	Min	Typ ²	Max	Unit	Spec ³ Perf
	BIAS CURRENT	VIOH = 0 V, 4 V					
303	VIOL Current Program Range,						
	IOL = 0 mA to 40 mA	VDUT = -0.5 V, +5.2 V	0	0 4.0		V	P
304	IOH, VIOL Input	VIOL = 0 V, 4 V and	VIOL = 0 V, 4 V and $-300 +300$			μA	P
305	IOXRTN Range	IOL = +40 mA, IOH = -40 mA, VDUT = -0.5 V, +6.5 V		-0.5, +6	5.5	V	N
310	VDUT Range	IOL = +40 mA, IOH = -40 mA, VDUT - VCOM > 1.3 V	-0.5		+6.5	V	P
311	VDUT Range, IOH = 0 mA to -40 mA	VDUT – VCOM > 1.3 V	0.8		6.5	V	P
312	VDUT Range, IOL = 0 mA to +40 mA	VCOM – VDUT > 1.3 V	-0.5		+5.2	V	P
	OUTPUT CHARACTERISTICS						
320	Accuracy Gain Error, Load Current, Normal Range Calculated at 1 mA and 40 mA points ²	IOL, IOH = 25 μ A – 40 mA, VCOM = 0 V, VDUT = \pm 2 V and IOL = 25 μ A to 40 mA, VCOM = +6.5 V, VDUT = +5.2 V and IOH = 25 μ A to 40 mA, VCOM =	-0.35		+0.35	%I _{SET}	P
321	Load Offset	-0.5 V, VDUT = +0.8 V Calculated from Intercept of 1 mA	-300		+300	μА	P
322 323	Load Nonlinearity Output Current Temperature	and 40 mA Points IOL, IOH from 25 μA to 40 mA Measured at IOH, IOL = 200 μA	-80	< ±3	+80	μΑ μΑ/°C	P N
324	COEFFICIENT IOH Extended Range	Driver Inhibited, IOH = 1 mA, Change in IOH from VTT = 0 V to VTT = -1.0 V	2			%	P
-	VCOM BUFFER						+
330	VCOM Buffer Offset Error	IOL, $IOH = 40$ mA, $VCOM = 0$ V	-50		+50	mV	P
331	VCOM Buffer Bias Current	VCOM = 0 V	-20		+20	μA	P
332	VCOM Buffer Gain Error	IOL, IOH = 40 mA, VCOM =	-4		+4	%	P
333	VCOM Buffer Linearity Error	-0.5 V to +6.5 V IOL, IOH = 40 mA, VCOMI = -0.5 V to +6.5 V	-10		+10	mV	P
	DYNAMIC PERFORMANCE						
	Propagation Delay						
340	± I _{MAX} to INHIBIT	VTT = +2 V, VCOM = +4/0 V, IOL = +20 mA, IOH = -20 mA	1.0	1.3	2.0	ns	P
341	INHIBIT to \pm I _{MAX}	VTT = +2 V, VCOM = +4/0 V, IOL = +20 mA, IOH = -20 mA	1.2 1.8 2.4		2.4	ns	P
342	Propagation Delay Matching	Matching = (Test 340 Value) – (Test 341 Value)	-1.0 +1.0		ns	P	
350	I/O Spike	VCOM = 0 V, IOL = +20 mA, IOH = -20 mA		250		mV	N
360	Settling Time to 15 mV	IOL = $+20$ mA, IOH = -20 mA, 50 Ω Load, to ± 15 mV		50		ns	N
361	Settling Time to 4 mV	IOL = $+20$ mA, IOH = -20 mA, 50 Ω Load, to ± 4 mV		10		μs	N

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DYNAMIC CLAMP PART¹

Spec No.	Parameter	Conditions	Min	Typ ²	Max	Unit	Spec ³ Perf
400	Input Voltage VCH		2		7.5	V	P
401	Input Voltage VCL		-1.5		+4	V	P
402	Input Bias Current VCH/VCL	Over range spec #401, 402	-250		+250	μA	P
410	VCH, VCL Offset Error	$I_{TEST} = 1 \text{ mA}$	-250		+250	mV	P
411	VCH, VCL Gain Error	$I_{TEST} = 1 \text{ mA}$	0.96		1.01	V/V	P
420	Static Current Capability		50		75	mA	N
430	Incremental Resistance	11 mA to 21 mA	45	48	52	Ω	P
440	VCHP, VCLP Protection		0.52		0.64	V	P
	Diodes Vf @ 500 μ						
441	Protection Diodes Max Current	For information only			2	mA	N
	TOTAL FUNCTION POWER DO	WN					
500	PWRD Input Voltage		0		5	V	P
501	PWRD Bias Current	PWRD trip point 1.4 V ± 0.15 V	-250		+250	μA	P
503	Power-Down Supply Reduction	VIOH = 0 V, VIOL = 0 V	35		60	%	P
504	Power-Down Output						
	Leakage Current	VIOH = 0 V, VIOL = 0 V, $V_{OUT} = -0.5 \text{ V to } +5.5 \text{ V}$	-20		+20	nA	P
505	Power-Down Output						
	Leakage Current	VIOH = 0 V, VIOL = 0 V, V _{OUT} = 5.5 V to 6.5 V	-500		+500	nA	P
600	Output Leakage Current,						
	$V_{OUT} = -0.5 \text{ V to } +6.5 \text{ V}$		-1		+1	μA	P
601	Output Leakage Current,						
	$V_{OUT} = 0 V \text{ to } 5 V$		-500		+500	nA	P
602	Output Leakage Current,						
	$V_{OUT} = -1 V$		-5		+5	μA	P
605	Output Capacitance	Driver and Load INHIBITED		9.2		pF	N
606	Output Capacitance Term	Driver VTERM = 0 V, Load INHIBITED		2.5		pF	N
	POWER SUPPLIES						
610	Total Supply Range			15		V	N
620	Positive Supply, VCC			+10.5		V	N
630	Negative Supply, VEE			-4.5		V	N
640	Positive Supply Current, VCC	Driver = Inhibit, I _{LOAD} program = 40 mA, Load = Active		465	570	mA	P
650	Negative Supply Current, VEE	Driver = Inhibit, I _{LOAD} program = 40 mA, Load = Active		475	600	mA	P
651	Comparator Supply Current	-					
	Overhead, VCCO	Driver = Inhibit, I _{LOAD} program = 40 mA, Load = Active (I _{VCCO} -			45	mA	P
660	Total Power Dissipation	(comparator logic output currents)) Driver = Inhibit, I _{LOAD} program =		7.2	7.9	W	P
661	Total Power Dissipation	40 mA, Load = Active Driver = Inhibit, I _{LOAD} program =		5.2	5.9	w	P
	-	0 mA		2. -	2.7	"	
700	Temperature Sensor					1	
	Gain Factor	$R_{LOAD} = 10 \text{ k}\Omega, V_{SOURCE} = 10.5 \text{ V}$		1		μA/K	N

NOTES

Specifications are subject to change without notice.

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 $^{^1}$ All temperature coefficients are measured at T_J = 75°C–95°C. In test figures, voltmeter loading is 1 MΩ or greater, scope probe loading is 100 kΩ in parallel with 0.6 pF. 2 Typical Values are not tested or guaranteed. Nominal values are generated from design or simulation analyses and/or limited bench evaluations and are not tested

²Typical Values are not tested or guaranteed. Nominal values are generated from design or simulation analyses and/or limited bench evaluations and are not tested or guaranteed.

³Spec Perf: N = Nominal, O = Operating Condition, T = Typical, P = Production, Max Min

⁴VTERM Linearity over the following condition: VL - 6 V < VTERM < VH + 6 V

⁵All ac input values are referred to the source end of transmission line input.

⁶All ac tests are performed with Driver in VTERM mode except where noted.

⁷Rise time is calculated SQRT((comp out rt)**2–(comp in rt)**2)

ABSOLUTE MAXIMUM RATINGS ¹
POWER SUPPLY VOLTAGE
V _{CC} to GND
V _{EE} to GND7 V
V_{CC} to V_{EE}
VCCO to GND
PWRGND, DRGND, GND_ROT, or HQGND ±0.4 V
OUTPUTS
V _{OUT} Short Circuit Duration Indefinite ²
V _{OUT} , Inhibit Mode +8.5 V, -2 V
V_{OUT} , Inhibit Mode $VL - 5.5 V < V_{OUT} < VH + 5.5 V$
VHDCPL Do Not Connect Except for Cap to V_{CC}
VLDCPL Do Not Connect Except for Cap to V_{EE}
QH, QHb, QL, QLB Maximum I _{OUT} :
Continuous 50 mA
Continuous 50 mA Surge 100 mA
Surge
Surge100 mATHERM11 V, 0 VDriver output capacitance, maximum10 pFINPUTS
Surge100 mATHERM11 V, 0 VDriver output capacitance, maximum10 pF
Surge100 mATHERM11 V, 0 VDriver output capacitance, maximum10 pFINPUTS
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INHL to INHLb
VH, VL, VTERM to GND (Rseries $< 500 \Omega$) . $+7.5 \text{ V}$, -1.1 V
VH to VL
$(VH-VTERM)$ and $(VTERM-VL)$ $\pm 8~V$
Reflection Clamps High/Low +8.5 V, -2 V
Protection Clamp Breakdown Voltage 12 V
Protection Clamps Current ±5 mA
V_{OUT} to HCOMP or LCOMP
ENVIRONMENTAL
Operating Temperature (Junction)
Storage Temperature65°C to +150°C
Lead Temperature (Soldering, 10 sec) ³ 260°C

NOTES

¹Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Absolute maximum limits apply individually, not in combination. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

²Output short circuit protection is guaranteed as long as proper heat sinking is employed to ensure compliance with the operating temperature limits.

 3 To ensure lead coplanarity (± 0.002 inches) and solderability, handling with bare hands should be avoided and the device should be stored in environments at 24 °C ± 5 °C (75°F ± 10 °F) with relative humidity not to exceed 65%.

ORDERING GUIDE

Model	Temperature	Package	Package
	Range	Description	Option
AD53522JSQ	0°C to 70°C	100-Lead LQFP-EDQUAD with Integral Heat Slug	SQ-100

CAUTION_

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the AD53522 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high-energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



Table I. Driver Truth Table

DATA	DATAb	IOD	IODb	RLD	RLDb	Output State
0	1	1	0	X	X	VL
1	0	1	0	X	X	VH
X	X	0	1	0	1	INH and
						CLAMP
X	X	0	1	1	0	VTERM

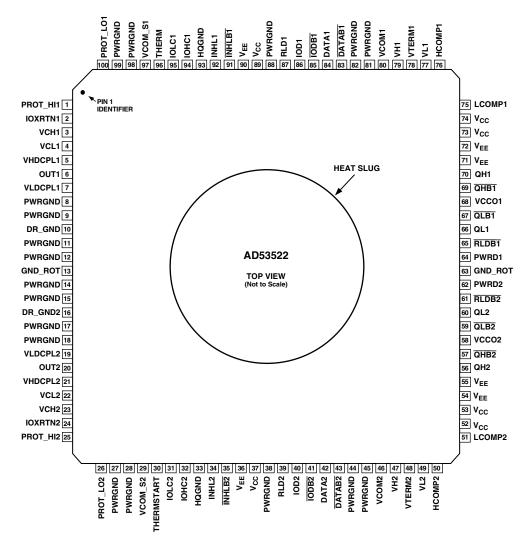
Table II. Comparator Truth Table

		Output States				
V _{OUT}		QH	QHb	QL	QLb	
> HCOMP	> LCOMP	1	0	1	0	
> HCOMP	< LCOMP	1	0	0	1	
< HCOMP	> LCOMP	0	1	1	0	
< HCOMP	< LCOMP	0	1	0	1	

Table III. Active Load Truth Table

			Output States (including diode bridge)					
VDUT	INHL	INHLb	ЮН	IOL	I(V _{OUT})			
<vcom< td=""><td></td><td>1</td><td>$V(IOHC) \times +10 \text{ mA}$</td><td>V(IOLC) × -10 mA</td><td>IOL</td></vcom<>		1	$V(IOHC) \times +10 \text{ mA}$	V(IOLC) × -10 mA	IOL			
>VCOM	0	1	$V(IOHC) \times +10 \text{ mA}$	$V(IOLC) \times -10 \text{ mA}$	IOH			
X	1	0	0	0	0			

PIN CONFIGURATION



NOTE DIE IS MOUNTED TO THE BACK OF THE HEAT SLUG. THE PACKAGE IS MOUNTED TO THE BOARD, HEAT SLUG UP.

PIN FUNCTION DESCRIPTIONS

Pin Number	Mnemonic	Description
1	PROT_HI1	Channel 1, output voltage sensing diode
2	IOXRTN1	Current return path for the active load for channel 1. Typically connected to a power ground.
3	VCH1	Analog input voltage that sets the reflection clamp high level of channel 1
4	VCL1	Analog input voltage that sets the reflection clamp low level of channel 1
5	VHDCPL1	Internal supply decoupling for the driver output stage of channel 1. This pin needs to be connected to $V_{\rm CC}$ through a 39 nF (minimum) capacitor.
6	OUT1	Input/output for the driver, window comparator, reflection clamp, and the active load of channel 1
7	VLDCPL1	Internal supply decoupling for the driver output stage of channel 1. This pin needs to be connected to $V_{\rm EE}$ through a 39 nF (minimum) capacitor.
8	PWRGND	Power ground
9	PWRGND	Power ground
10	DR_GND	Analog ground

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Pin Number	Mnemonic	Description
11	PWRGND	Power ground
12	PWRGND	Power ground
13	GND_ROT	Analog ground
14	PWRGND	Power ground
15	PWRGND	Power ground
16	DR_GND	Analog ground
17	PWRGND	Power ground
18	PWRGND	Power ground
19	VLDCPL2	Internal supply decoupling for the driver output stage of channel 2. This pin needs to be connected to V_{EE} through a 39 nF (minimum) capacitor.
20	OUT2	Input/output for the driver, window comparator, reflection clamp, and the active load of channel 2
21	VHDCPL2	Internal supply decoupling for the driver output stage of channel 2. This pin needs to be connected to V_{CC} through a 39 nF (minimum) capacitor.
22	VCL2	Analog input voltage that sets the reflection clamp high level of channel 2
23	VCH2	Analog input voltage that sets the reflection clamp high level of channel 2
24	IOXRTN2	Current return path for the active load for channel 2. Typically connected to a power ground.
25	PROT_HI2	Channel 2, output voltage sensing diode
26	PROT_LO2	Channel 2, output voltage sensing diode
27	PWRGND	Power ground
28	PWRGND	Power ground
29	VCOM_S2	Analog output voltage that represents a buffered VCOM1 input
30	THERMSTART	Temperature sensor startup pin. Normally not connected
31	IOLC2	Analog input voltage that programs the channel 2 active load source current
32	IOHC2	Analog input voltage that programs the channel 2 active load sink current
33	HQGND	Clean analog ground for the active load for channel 2
34	INHL2	One of two complementary inputs that control the inhibit mode for the active load bridge of channel 2
35	ĪNHLB2	One of two complementary inputs that control the inhibit mode for the active load bridge of channel 2
36	V_{EE}	Negative supply terminal
37	V _{CC}	Positive supply terminal
38	PWRGND	Power ground
39	RLD2	One of two complementary inputs that control, in conjunction with IOD2 and IODB2, the operating mode of the channel 2 driver. Refer to the Driver Truth Table for specific conditions.
40	IOD2	One of two complementary inputs that control, in conjunction with RLD2 and RLDB2, the operating mode of the channel 2 driver. Refer to the Driver Truth Table for specific conditions.
41	ĪODB2	One of two complementary inputs that control, in conjunction with RLD2 and RLDB2, the operating mode of the channel 2 driver. Refer to the Driver Truth Table for specific conditions.
42	DATA2	One of two complementary input that determine the high and low state of the channel 2 driver. Driver output is high for DATA2 > DATAB2. Refer to the Driver Truth Table for specific conditions.
43	DATAB2	One of two complementary input that determine the high and low state of the channel 2 driver. Driver output is high for DATA2 > DATAB2. Refer to the Driver Truth Table for specific conditions.
44	PWRGND	Power ground
45	PWRGND	Power ground
46	VCOM2	Analog input voltage that establishes the commutation voltage for the active load diode bridge for channel 2
47	VH2	Analog input voltage that sets the Logic 1 level of the driver output limit for channel 2. Determines the driver output for DATA2 > DATAB

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Pin Number	Mnemonic	Description
48	VTERM2	Analog input voltage that sets the termination voltage level of the channel 2 driver when in VTERM mode
49	VL2	Analog input voltage that sets the Logic 0 level of the driver output limit for channel 2. Determines the driver output for DATAB2 > DATA2.
50	HCOMP2	Analog input voltage that sets the Logic 1 compare reference for the window comparator of channel 2
51	LCOMP2	Analog input voltage that sets the Logic 0 compare reference for the window comparator of channel 2
52	V_{CC}	Positive supply terminal
53	V_{CC}	Positive supply terminal
54	V_{EE}	Negative supply terminal
55	V_{EE}	Negative supply terminal
56	QH2	One of two complementary outputs for the Logic 1 window comparator of channel 1
57	QHB2	One of two complementary outputs for the Logic 1 window comparator of channel 1
58	VCCO2	Input supply voltage for QH2, QHB2, QL2, and QLB2 signals and reference voltage for DATA2, DATAB2, IOD2, IODB2, RLD2, and RLDB2
59	QLB2	One of two complementary outputs for the Logic 0 window comparator of channel 2
60	QL2	One of two complementary outputs for the Logic 0 window comparator of channel 2
61	RLDB2	One of two complementary inputs that control, in conjunction with IOD2 and IODB2, the operating mode of the channel 2 driver. Refer to the Driver Truth Table for specific conditions.
62	PWRD2	Power-down control for channel 2
63	GND_ROT	Analog ground
64	PWRD1	Power-down control for channel 1
65	RLDB1	One of two complementary inputs that control, in conjunction with IOD1 and IODB1, the operating mode of the channel 1 driver
66	QL1	One of two complementary outputs for the Logic 0 window comparator of channel 1
67	QLB1	One of two complementary outputs for the Logic 0 window comparator of channel 1
68	VCCO1	Input supply voltage for QH1, QHB1, QL1, and QLB1 signals and reference voltage for DATA1, DATAB1, IOD1, IODB1, RLD1, and RLDB1
69	QHB1	One of two complementary outputs for the Logic 1 window comparator of channel 1
70	QH1	One of two complementary outputs for the Logic 1 window comparator of channel 1
71	V_{EE}	Negative supply terminal
72	V_{EE}	Negative supply terminal
73	V_{CC}	Positive supply terminal
74	V_{CC}	Positive supply terminal
75	LCOMP1	Analog input voltage that sets the Logic 0 compare reference for the window comparator of channel 1
76	HCOMP1	Analog input voltage that sets the Logic 1 compare reference for the window comparator of channel 1
77	VL1	Analog input voltage that sets the Logic 0 level of the driver output limit for channel 1. Determines the driver output for DATAB1 > DATA1.
78	VTERM1	Analog input voltage that sets the termination voltage level of the channel 1 driver when in VTERM mode
79	VH1	Analog input voltage that sets the Logic 1 level of the driver output limit for channel 1. Determines the driver output for DATA1 > DATAB1.
80	VCOM1	Analog input voltage that establishes the commutation voltage for the active load diode bridge for channel 1
81	PWRGND	Power ground
82	PWRGND	Power ground
83	DATAB1	One of two complementary inputs that determine the high and low state of the channel 1 driver. Driver output is high for DATA1 > DATAB1. Refer to the Driver Truth Table for specific conditions.
84	DATA1	One of two complementary inputs that determine the high and low state of the channel 1 driver. Driver output is high for DATA1 > DATAB1. Refer to the Driver Truth Table for specific conditions.

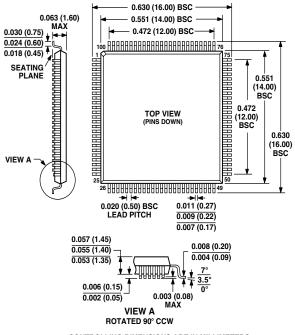
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Pin Number	Mnemonic	Description
85	ĪODB1	One of two complementary inputs that control, in conjunction with RLD1 and RLDB1, the operating mode of the channel 1 driver. Refer to the Driver Truth Table for specific conditions.
86	IOD1	One of two complementary inputs that control, in conjunction with RLD1 and RLDB1, the operating mode of the channel 1 driver. Refer to the Driver Truth Table for specific conditions.
87	RLD1	One of two complementary inputs that controls, in conjunction with IOD1 and IODB1, the operating mode of the channel 1 driver. Refer to the Driver Truth Table for specific conditions.
88	PWRGND	Power ground
89	V_{CC}	Positive supply terminal
90	V_{EE}	Negative supply terminal
91	ĪNHLB1	One of two complementary inputs that control the inhibit mode for the active load bridge of channel 1
92	INHL1	One of two complementary inputs that control the inhibit mode for the active load bridge of channel 1
93	HQGND	Clean analog ground for the active load for channel 1
94	IOHC1	Analog input voltage that programs the channel 1 active load sink current
95	IOLC1	Analog input voltage that programs the channel 1 active load source current
96	THERM	Temperature sensor output pin. A resistor (10 KW) should be connected between THERM and $V_{\rm CC}$. The approximate die temperature can be determined by measuring the current through the resistor. The typical scale factor is $1\mu A/K$.
97	VCOM_S1	Analog output voltage that represents a buffered VCOM1 input
98	PWRGND	Power ground
99	PWRGND	Power ground
100	PROT_LO1	Channel 1 output voltage sensing diode

OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

100-Lead LQFP-EDQUAD (SQ-100)



CONTROLLING DIMENSIONS ARE IN MILLIMETERS.

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